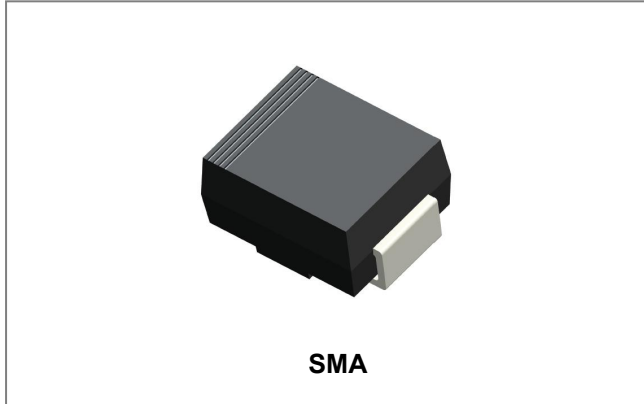


RS1A-RS1M SURFACE MOUNT SUPER FAST RECTIFIER



Features

- The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- For surface mounted applications
- Fast switching for high efficiency
- Low reverse leakage
- Built-in strain relief, ideal for automated placement
- High forward surge current capability
- High temperature soldering guaranteed:
250 °C/10 seconds at terminals
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: SMA molded plastic body
- Terminals: Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 0.06 grams

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Type Number	Symbol	RS1A	RS1B	RS1D	RS1G	RS1J	RS1K	RS1M	Units	
Peak Repetitive Reverse Voltage	V _{RRM}									
Working Peak Reverse Voltage	V _{RWM}	50	100	200	400	600	800	1000	V	
DC Blocking Voltage	V _{DC}									
RMS Reverse Voltage	V _{RMS}	35	70	140	280	420	560	700	V	
Average forward rectified output current @T _L = 90°C	I _o	1.0								A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	30								A
Forward Voltage @I _F =1.0A	V _F	1.3								V
Peak Reverse Current @T _A = 25°C	I _{RM}	5.0								µA
At Rated DC Blocking Voltage @T _A = 100°C		50								
Maximum Reverse Recovery Time (Note 1)	T _{rr}	150				250	500		ns	
Typical Junction Capacitance (Note 2)	C _J	15								pF
Typical Thermal Resistance Junction to Ambient (Note 3)	R _{θJA}	50								°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150								°C

Note: 1. Reverse recovery condition I_F=0.5A, I_R=1.0A, I_{rr}=0.25A
2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
3. Mounted on P.C.B.with 8.0mm² land areas.

- China - Germany - Korea - Singapore - United States •
- <http://www.smc-diodes.com> - sales@smc-diodes.com •

Ratings and Characteristics Curves

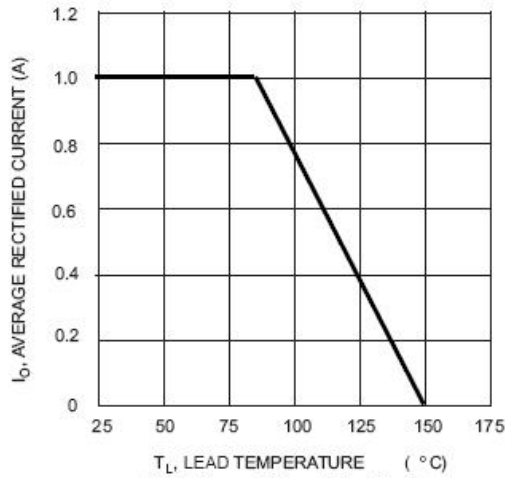


Fig. 1 Forward Current Derating Curve

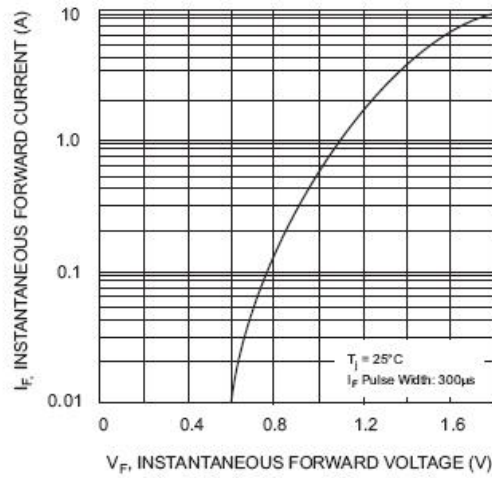


Fig. 2 Typical Forward Characteristics

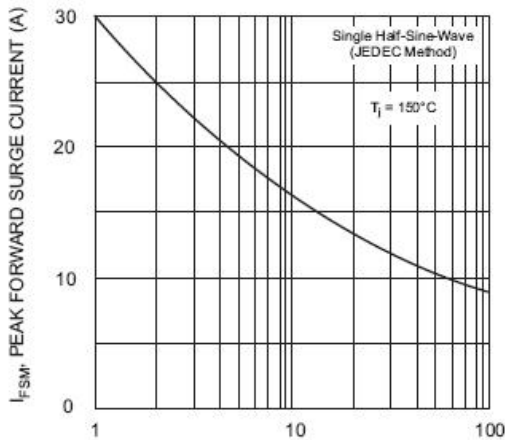


Fig. 3 Forward Surge Current Derating Curve

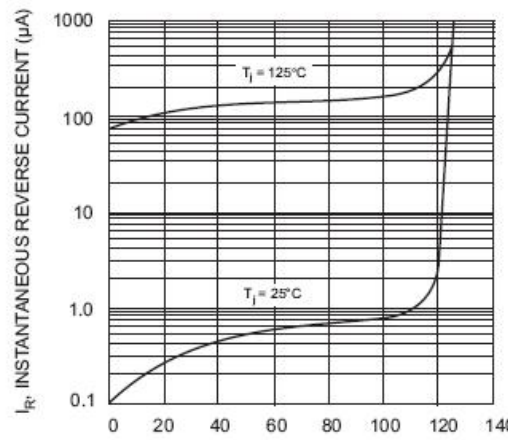
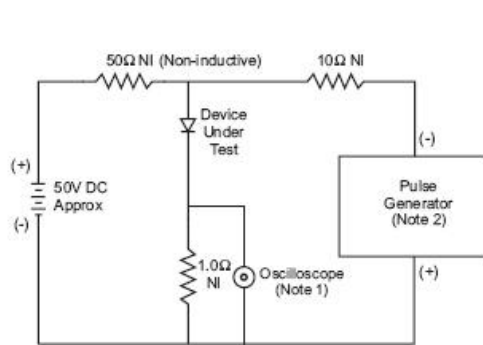


Fig. 4 Typical Reverse Characteristics



Notes:
1. Rise Time = 7.0ns max. Input Impedance = 1.0MΩ, 22pF.
2. Rise Time = 10ns max. Input Impedance = 50Ω.

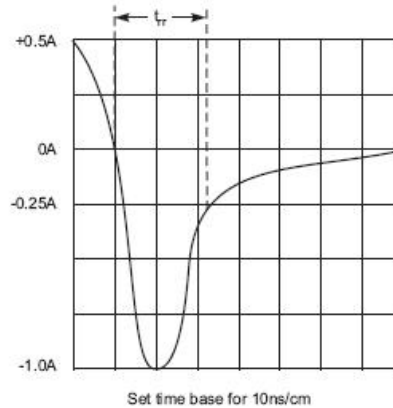
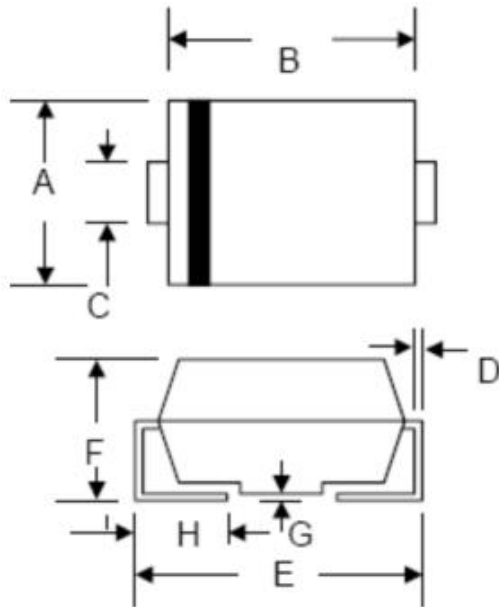


Fig. 5 Reverse Recovery Time Characteristic and Test Circuit

Mechanical Dimensions SMA



SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.40	2.84	0.094	0.112
B	3.99	4.75	0.157	0.187
C	1.05	1.70	0.041	0.067
D	0.15	0.51	0.006	0.020
E	4.80	5.66	0.189	0.223
F	1.90	2.95	0.075	0.116
G	0.05	0.203	0.002	0.008
H	0.76	1.52	0.030	0.600

Ordering Information

Device	Package	Shipping
RS1A-RS1M	SMA (Pb-Free)	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram

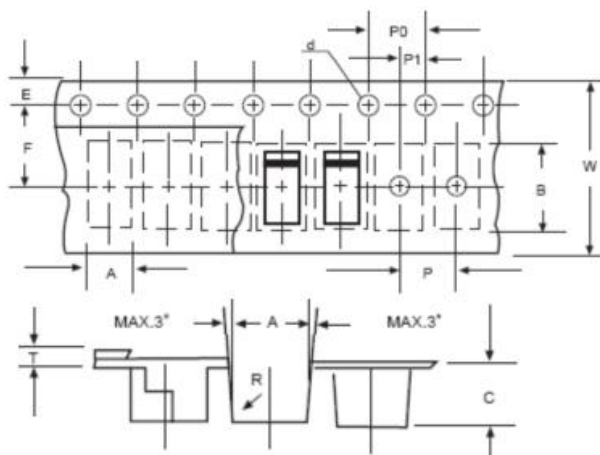


Where XXXXX is YYWWL

RS1A = Type Number
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Carrier Tape Specification SMA



SYMBOL	Millimeters	
	Min.	Max.
A	2.97	3.17
B	5.70	5.90
C	2.32	2.52
d	1.40	1.60
E	1.40	1.60
F	5.60	5.70
P	3.90	4.10
P0	3.90	4.10
P1	1.90	2.10
T	0.25	0.35
W	11.80	12.20

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